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NTE2698 Silicon NPN Transistor General Purpose TO3PN Type Package

Features:

- Low Collector Saturation Voltage: $V_{CE(sat)} = 0.5V$ Max @ $I_C = 3A$
- Collector–Emitter Breakdown Voltage: $V_{(BR)CEO} = 120V$ Min
- Good Linearity of h_{FE}

Applications:

- Humidifier
- DC/DC Converter
- General Purpose Power Amplifiers

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	200V
Collector–Emitter Voltage, V_{CEO}	120V
Emitter–Base Voltage, V_{EBO}	8V
Collector Current, I_C	
Continuous	7A
Pulse	14A
Continuous Base Current, I_B	3A
Collector Power Dissipation ($T_C = +25^\circ C$), P_C	70W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50mA, I_B = 0$	120	–	–	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 300mA$	–	–	0.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 3A, I_B = 300mA$	–	–	1.2	V
Collector Cut–Off Current	I_{CBO}	$V_{CB} = 200V, I_E = 0$	–	–	100	μA
Emitter Cut–Off Current	I_{EBO}	$V_{EB} = 8V, I_C = 0$	–	–	100	μA
DC Current Gain	h_{FE}	$I_C = 3A, V_{CE} = 4V$	100	–	200	



